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FDP120N10 N-Channel PowerTrench[®] MOSFET 100 V, 74 A, 12 mΩ

Features

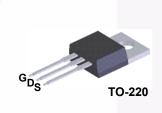
- $R_{DS(on)}$ = 9.7 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 74 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

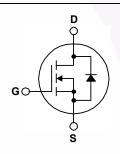
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micor Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDP120N10	Unit	
V _{DSS}	Drain to Source Voltage			100	V	
V _{GSS}	Gate to Source Voltage			±20	V	
ID	Drain Current	- Continuous (T _C = 25 ^o C)		74	•	
	Drain Current	- Continuous (T _C = 100 ^o C)		52	- A	
I _{DM}	Drain Current	- Pulsed (N	lote 1)	296	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		Note 2)	198	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		Note 3)	6.0	V/ns	
P _D	Dower Dissinction	(T _C = 25°C)		170	W	
	Power Dissipation	- Derate Above 25°C		1.14	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		ds	300	°C	

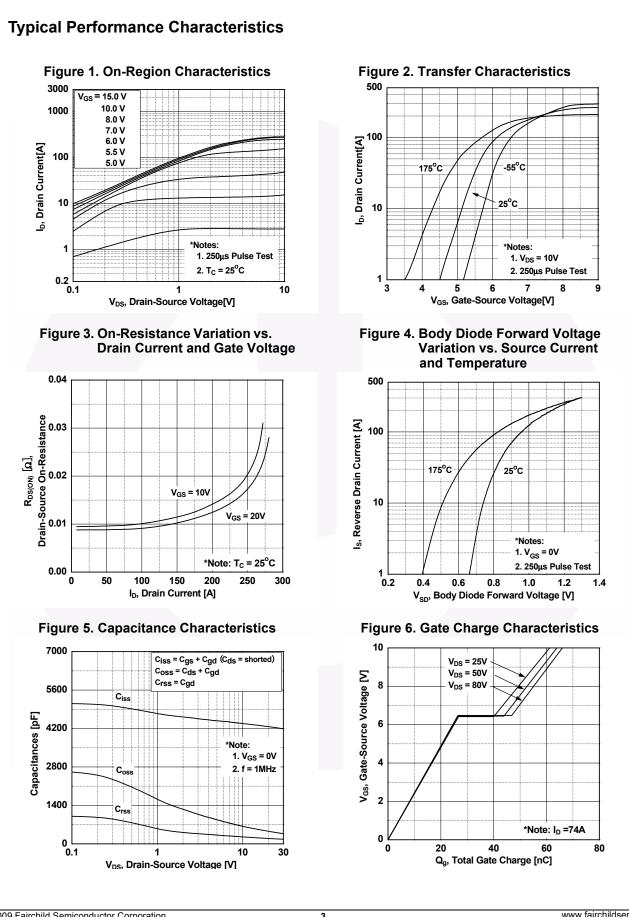
Thermal Characteristics

Symbol	Parameter	FDP120N10	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.88	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0.00

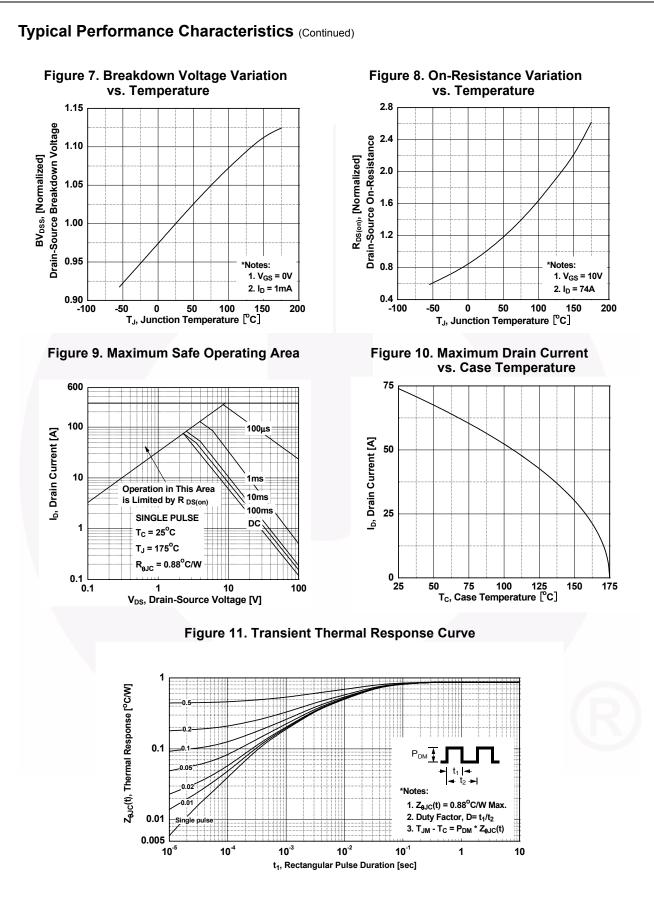
November 2013

Top Mark N10 FDP120N10 I Characteristics Togethered Parameter Parameter	TO-2							ntity
Parameter	= 25°C unles	1000	kagePacking MethodReel Size-220TubeN/A		Tape Width N/A		50 units	
		s otherwise noted.			- 1			
teristics		Test C	onditions		Min.	Тур.	Max.	Unit
	_					_		
Drain to Source Breakdown	Voltage	I _D = 250 μA, V _{GS}	= 0 V, T _C	= 25°C	100	-	_	V
Breakdown Voltage Temper	-					0.1		V/ºC
Coefficient	Coefficient		25°C	-	0.1	-	V/-C	
Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V			-	-	1	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_{C} = 150°C			-	-	500	μΑ
Gate to Body Leakage Current		$V_{GS} = \pm 20 V, V_{DS} = 0 V$			-	-	±100	nA
teristics								
		Vcs = Vps. lp =	250 цA		2.5	-	4.5	V
-	esistance				-	9.7		mΩ
					-	-	-	S
		.03				100		-
haracteristics								
Input Capacitance		N 05 X X 0 X			-	4215	5605	pF
Output Capacitance			= 0 V,		-	405	540	pF
Reverse Transfer Capacitar	ice				-	170	255	pF
Total Gate Charge at 10V		Vne = 80 V In =	74 A.		-	66	86	nC
Gate to Source Gate Charg	е	$V_{GS} = 10 V$,		-	26	-	nC
Gate to Drain "Miller" Charg	e			(Note 4)	-	20	-	nC
Characteristics								
1						27	64	ne
,		Voo = 50 V lo =	74 A	-	-			ns
				-	-			ns
					-	39 15	40	ns
Turn Off Fall Time				(Note 4)	-	15	40	ns
Turn-Off Fall Time								
Turn-Off Fall Time	ics							
		de Forward Current			-	-	74	Α
rce Diode Characterist Maximum Continuous Drain	to Source Dic				-	-		A A
rce Diode Characterist	to Source Dic ource Diode F	orward Current			-	-	74 296 1.3	A A V
rce Diode Characterist Maximum Continuous Drain Maximum Pulsed Drain to S	to Source Dic ource Diode F		74 A			- - - 44	296	Α
	Gate to Body Leakage Curre teristics Gate Threshold Voltage Static Drain to Source On R Forward Transconductance characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitan Total Gate Charge at 10V Gate to Source Gate Charge	Gate to Body Leakage Current Gate to Body Leakage Current teristics Gate Threshold Voltage Static Drain to Source On Resistance Forward Transconductance Faracteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Total Gate Charge at 10V Gate to Drain "Miller" Charge Characteristics Turn-On Delay Time Turn-On Rise Time	Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}, V_G$ Gate to Body Leakage Current $V_{GS} = 100 \text{ V}, V_G$ teristics Gate Threshold Voltage $V_{GS} = \pm 20 \text{ V}, V_D$ Static Drain to Source On Resistance $V_{GS} = 10 \text{ V}, I_D =$ Forward Transconductance $V_{DS} = 10 \text{ V}, I_D =$ Eharacteristics Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS}$ Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS}$ $f = 1 \text{ MHz}$ Reverse Transfer Capacitance $V_{DS} = 80 \text{ V} I_D =$ $V_{GS} = 10 \text{ V}$ Gate to Source Gate Charge $V_{GS} = 10 \text{ V}$ $V_{GS} = 10 \text{ V}$ Gate to Drain "Miller" Charge $V_{DD} = 50 \text{ V}, I_D =$ $V_{DD} = 50 \text{ V}, I_D =$ Turn-On Delay Time $V_{DD} = 50 \text{ V}, I_D =$ $V_{DD} = 50 \text{ V}, I_D =$	Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_C$ Gate to Body Leakage Current $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ teristicsGate Threshold Voltage $V_{GS} = V_{DS}, I_D = 250 \mu \text{A}$ Static Drain to Source On Resistance $V_{GS} = 10 \text{ V}, I_D = 74 \text{ A}$ Forward Transconductance $V_{DS} = 10 \text{ V}, I_D = 74 \text{ A}$ EharacteristicsInput CapacitanceInput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ Reverse Transfer Capacitance $V_{DS} = 80 \text{ V} I_D = 74 \text{ A}, V_{GS} = 10 \text{ V}$ Gate to Source Gate Charge 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0 \text{ V}$ teristics $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$ Gate Threshold Voltage $V_{GS} = 10 \text{ V}, I_D = 74 \text{ A}$ Static Drain to Source On Resistance $V_{GS} = 10 \text{ V}, I_D = 74 \text{ A}$ Forward Transconductance $V_{DS} = 10 \text{ V}, I_D = 74 \text{ A}$ CharacteristicsInput CapacitanceInput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ Reverse Transfer Capacitance $V_{DS} = 80 \text{ V} \text{ I}_D = 74 \text{ A}, V_{GS} = 10 \text{ V} $ Gate to Source Gate Charge $V_{DS} = 80 \text{ V} \text{ I}_D = 74 \text{ A}, V_{GS} = 10 \text{ V}$ Gate to Drain "Miller" Charge $V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, 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= 0 \text{ V}, T_C = 150^{\circ}\text{C}$ -Gate to Body Leakage Current $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ -teristicsGate Threshold Voltage $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$ 2.5Static Drain to Source On Resistance $V_{GS} = 10 \text{ V}, I_D = 74 \text{ A}$ -Forward Transconductance $V_{DS} = 10 \text{ V}, I_D = 74 \text{ A}$ -Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ -Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ -Reverse Transfer Capacitance $r = 1 \text{ MHz}$ -Total Gate Charge at 10V $V_{DS} = 80 \text{ V} I_D = 74 \text{ A}, V_{GS} = 10 \text{ V}$ -Gate to Drain "Miller" Charge $V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 50 \text{ V}, I_D = 74 \text{ A}, V_{DD} = 74 \text{ A}, V_$	Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$ -Gate to Body Leakage Current $V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$ teristicsGate Threshold Voltage $V_{GS} = V_{DS}, \text{ I}_D = 250 \mu\text{A}$ 2.5-Static Drain to Source On Resistance $V_{GS} = 10 \text{ V}, \text{ I}_D = 74 \text{ A}$ -9.7Forward Transconductance $V_{DS} = 10 \text{ V}, \text{ I}_D = 74 \text{ A}$ -105tharacteristicsInput Capacitance $V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ -4215Output Capacitance $V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ -405Reverse Transfer Capacitance $f = 1 \text{ MHz}$ -105Total Gate Charge at 10V $V_{DS} = 80 \text{ V} \text{ I}_D = 74 \text{ A},$ -26Gate to Source Gate Charge $V_{GS} = 10 \text{ V}$ -20CharacteristicsTurn-On Delay Time $V_{DD} = 50 \text{ V}, \text{ I}_D = 74 \text{ A},$ -27Turn-On Rise Time $V_{DD} = 50 \text{ V}, \text{ I}_D = 74 \text{ A},$ -105	$\begin{array}{ c c c c c c c } \hline 2 \mbox{Current} & \hline V_{DS} = 100 \ V, \ V_{GS} = 0 \ V, \ T_C = 150^{\circ} \ C & - & - & 500 \\ \hline \hline Gate to Body Leakage Current & V_{GS} = \pm 20 \ V, \ V_{DS} = 0 \ V & - & - & \pm 100 \\ \hline \hline \mbox{teristics} & & & & & & & & & & & & & & & & & & &$

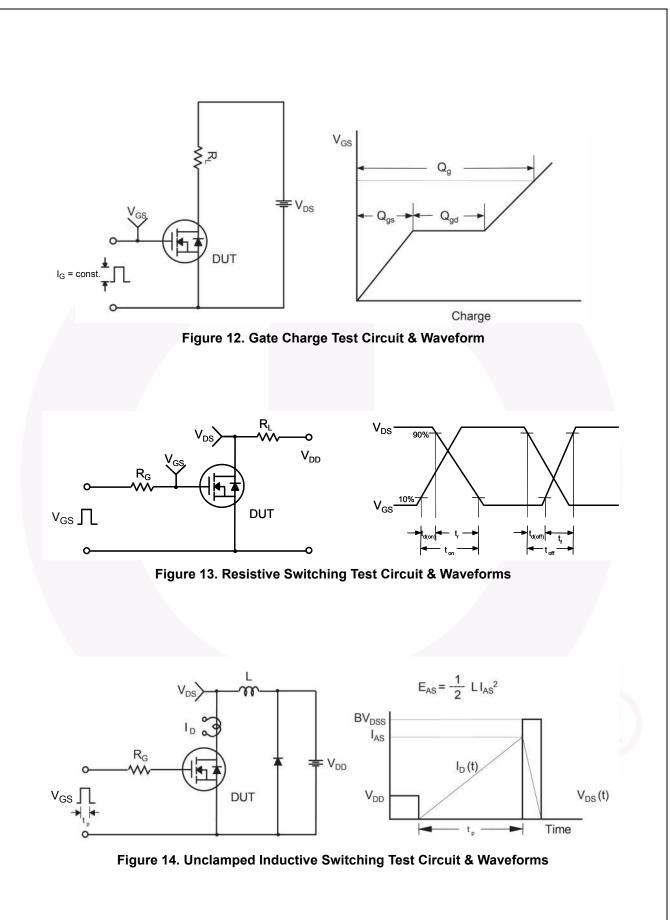
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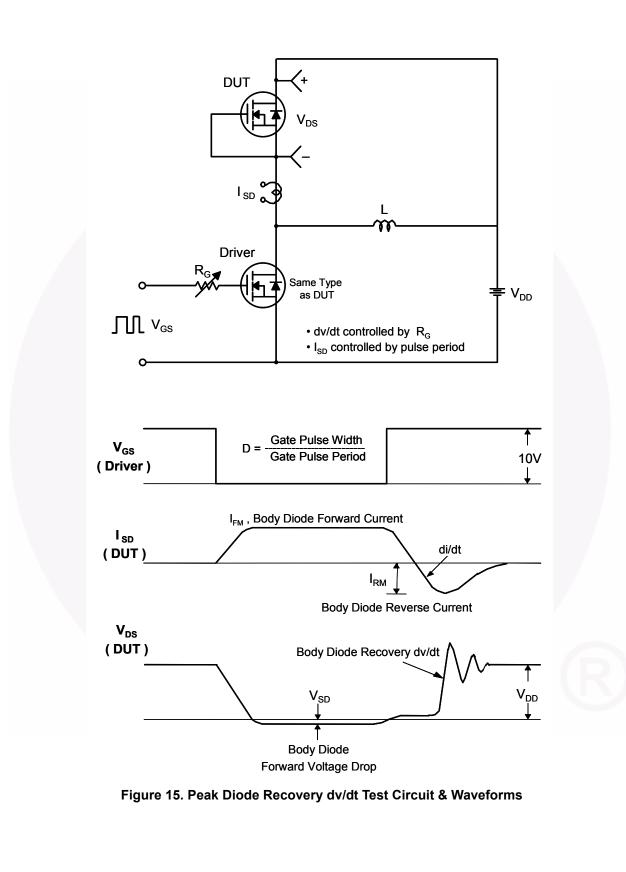


FDP120N10 — N-Channel PowerTrench[®] MOSFET



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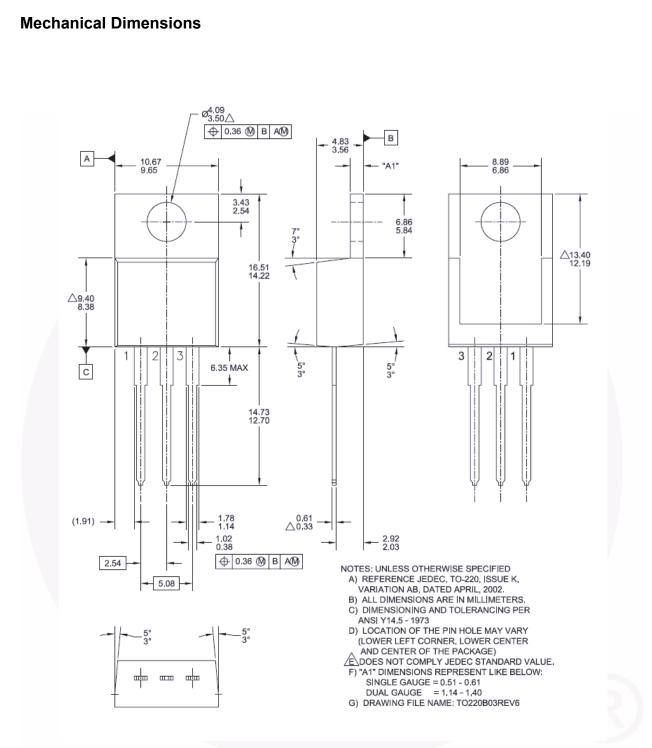


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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